

PROBLEM SET #5

Issued: Tuesday, Feb. 24, 2009

Due: Tuesday, March 3, 2009, 6:00 p.m. in the EE 140 homework box in 240 Cory

1. Razavi, Chapter 5: Problem 5.2.
2. Design the Widlar current source shown in Figure PS5.2 to produce 5 μA output current. Use identical transistors, $V_{CC} = 30\text{V}$, and $R_1 = 30\text{ k}\Omega$. Find the output resistance.

BJT Parameters: $\beta = 200$, $V_A = 130\text{ V}$, $V_{BE,ON} = 0.7\text{ V}$

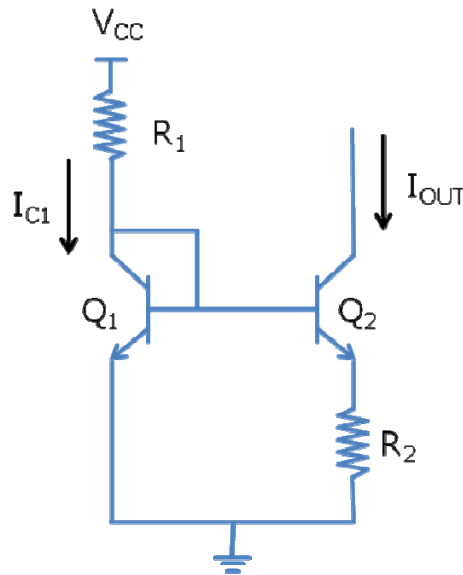


Figure PS5.2

3. This problem concerns the simple MOS current mirror shown in Figure PS5.3a.

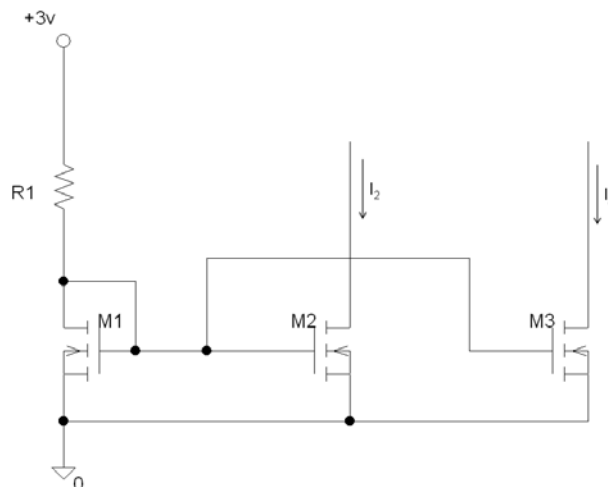


Figure PS5.3a

(a) Design the current mirror such that all of the following is satisfied:

- The currents $I_2=0.5\text{mA}$ and $I_3=2\text{mA}$ (approximately).
- The minimum output voltage for which M_2 and M_3 work as current sources is 200mV.
- The output currents change less than 1% for a change in output voltage of 1V.
- All transistors should have the same channel length.

You are to minimize the total circuit area which is approximately given by

$$A = \sum_{i=1}^3 W_i L_i + \beta R_1$$

The parameter λ can be calculated as $\lambda = \frac{\alpha}{L}$. α and β are constants.

$$\alpha = 0.02 \frac{\mu\text{m}}{\text{V}}, \quad \beta = 0.2 \frac{\mu\text{m}^2}{\Omega}, \quad C_{ox} = 5 \frac{\text{fF}}{\mu\text{m}^2}, \quad \mu_n = 450 \frac{\text{cm}^2}{\text{Vs}}, \quad V_{th0} = 0.6\text{V}$$

(b) A layout designer used long and narrow wires to connect sources of M_1 , M_2 , and M_3 , which resulted in small parasitic resistances $R_p=2\Omega$, as shown in Figure PS5.3b. What are the new values of I_2 and I_3 ? You can use numerical methods if needed.

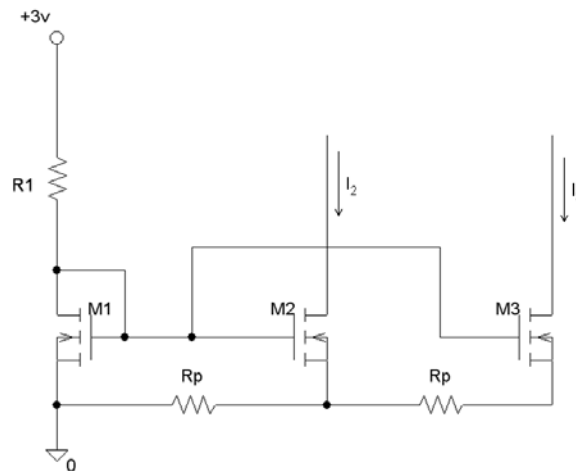


Figure PS5.3b

- Razavi, Chapter 5: Problem 5.6.
- Design the circuit shown in Figure PS5.5 to meet the following constraints:
 - Transistor M_2 operates in the saturated region for values of V_{OUT} to within 0.2 V of ground.
 - The output current must be 50 μA .
 - The output current must change less than 0.02% for a change in output voltage of 1 V.

You are to minimize the total device area within the given constraints. Here the device area will be taken to be the total gate area ($W \times L$ product). Ignore the body effect for simplicity.

Make all devices identical except M_4 . Use SPICE to check your design and also to plot the I_{OUT} - V_{OUT} characteristic for V_{OUT} from 0 to 3 V. Use the following process parameters: $t_{ox}=8$ nm, $\mu_n=450$ cm²/VS, $L_d=0.09$ μ m, $dX_d/dV_{DS}=0.02$ μ m/V (channel length modulation parameter, use it to get λ).

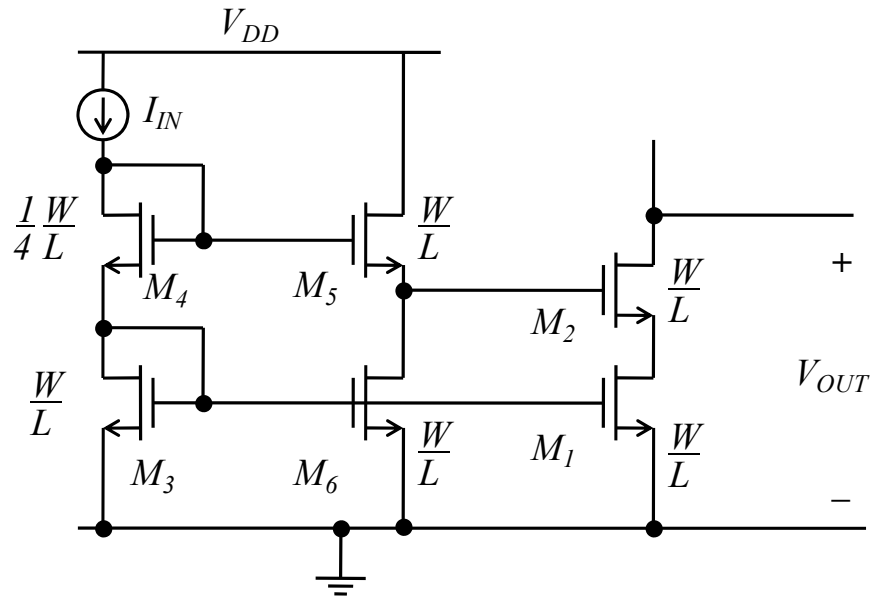


Figure PS5.5